

ETCH WITH RAMPING

ABSTRACT OF THE DISCLOSURE

5 A method for etching a feature in an etch layer through a mask over a
substrate. The substrate is placed in a process chamber. An etch plasma is
provided to the process chamber, where the etch plasma begins to etch. A feature
is etched in the etch layer with the etch plasma. At least one etch plasma
parameter is ramped during the etching of the feature to optimize plasma
parameters with the changing etch depth and the feature is etched with the ramped
10 plasma until the feature is etched to a feature depth.